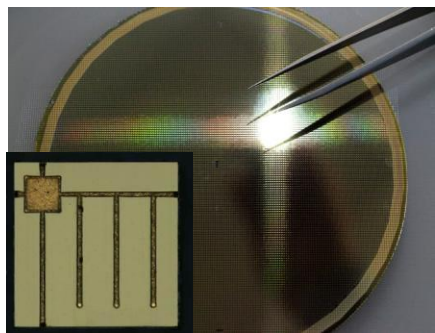


RCLED-960-6

High Power RCLED Chip – 6mW @ 960nm



Features:

- InGaAs/AlGaAs RCLED chip
- Reduced spectral width and enhanced power due to resonant cavity structure
- RoHS compliant

Applications:

- Pulse oximetry: Total Hemoglobin, Oxygen Content, Carboxyhemoglobin, Methemoglobin

Specification

DATE: 14th Feb. 2014

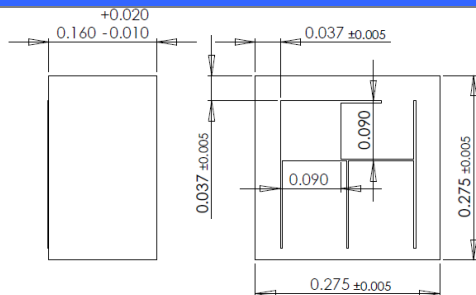
SPECIFICATIONS

Test conditions: CW operation at temperature of 25°C

Parameters	Symb.	Min.	Typ.	Max.	Unit
Operating current	I_{op}			200	mA
Operating voltage	V_{op}		1.5	2.0	V
Reverse voltage	V_{rev}			2.0	V
Optical output power at 100mA	P_{out}	5	6*		mW
Centroid wavelength	λ_C	955	960	965	nm
FWHM of spectrum	$\Delta\lambda$	30	40	50	nm
Operating temperature range	T_{op}	15		60	°C
Chip soldering temperature (20sec)	T_{sol}			330	°C

*up to 15 mW on request

DIMENSIONS in mm

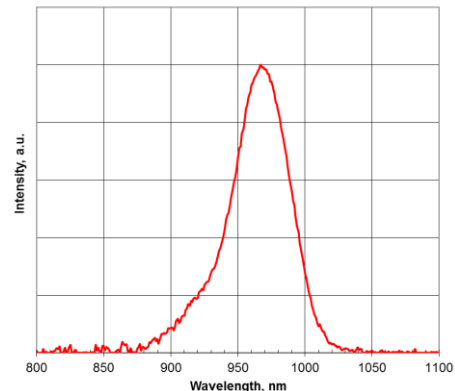
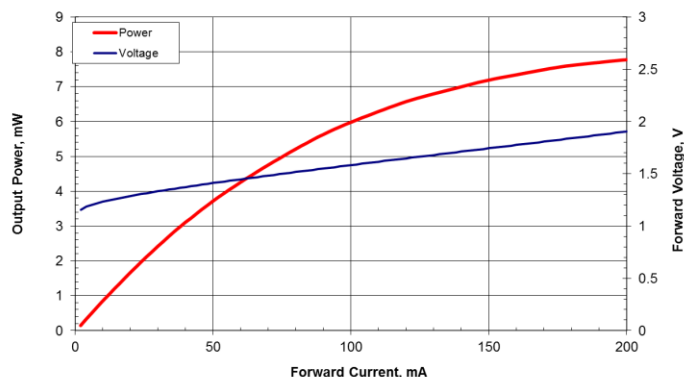


Design:

P-side up;

wire-bondable Au bond pad with current spreaders on top side;

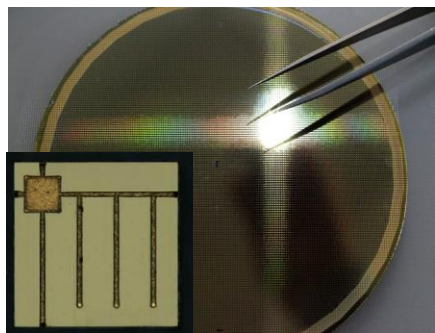
back-side full (100%) area metallization, Au-finished, solderable



NOTE: Innolume product specifications are subject to change without notice

RCLED-930-15

High Power RCLED Chip – 15mW @ 930nm



Features:

- InGaAs/AlGaAs RCLED chip
- Reduced spectral width and enhanced power due to resonant cavity structure
- RoHS compliant

Applications:

- Pulse oximetry: Total Hemoglobin, Oxygen Content, Carboxyhemoglobin, Methemoglobin

Specification

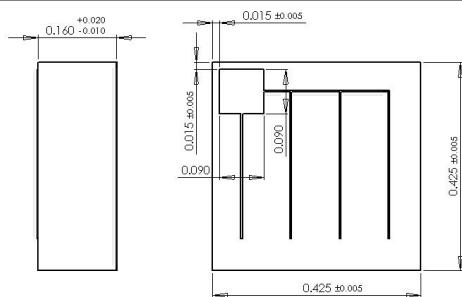
DATE: 14th Feb. 2014

SPECIFICATIONS

Test conditions: CW operation at temperature of 25°C

Parameters	Symb.	Min.	Typ.	Max.	Unit
Operating current	I_{op}			200	mA
Operating voltage	V_{op}		1.5	2.0	V
Reverse voltage	V_{rev}			2.0	V
Optical output power at 100mA	P_{out}	10	15		mW
Centroid wavelength	λ_C	920	930	940	nm
FWHM of spectrum	$\Delta\lambda$	30	40	50	nm
Operating temperature range	T_{op}	15		60	°C
Chip soldering temperature (20sec)	T_{sol}			330	°C

DIMENSIONS in mm

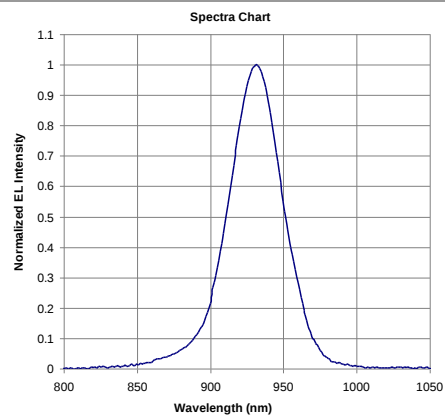
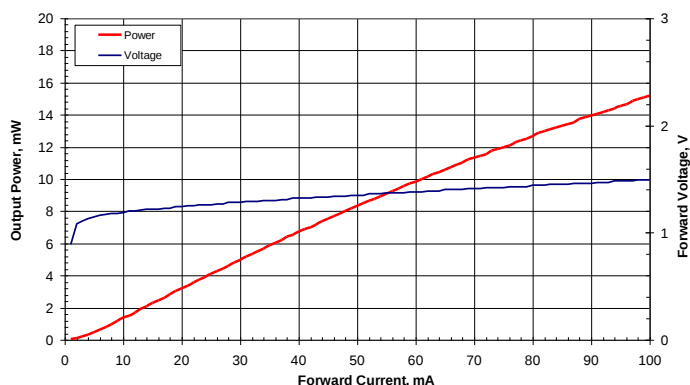


Design:

P-side up;

wire-bondable Au bond pad with current spreaders on top side;

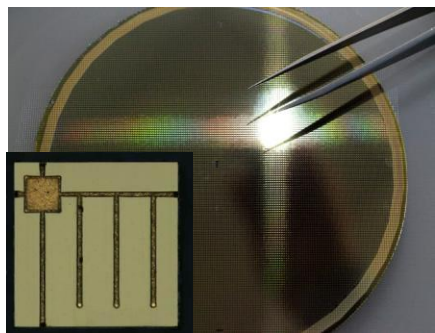
back-side full (100%) area metallization, Au-finished, solderable



NOTE: Innolume product specifications are subject to change without notice

RCLED-1170-10

High Power RCLED Chip – 10mW @ 1170nm



Features:

- InGaAs/AlGaAs RCLED chip
- Reduced spectral width and enhanced power due to resonant cavity structure
- Unique wavelength range
- RoHS compliant

Applications:

- Pulse oximetry: Total Hemoglobin, Oxygen Content, Carboxyhemoglobin, Methemoglobin

Specification

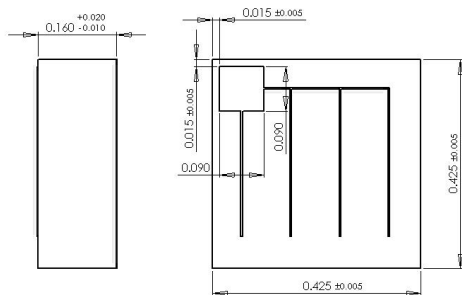
DATE: 14th Feb. 2014

SPECIFICATIONS

Test conditions: CW operation at temperature of 25°C

Parameters	Symb.	Min.	Typ.	Max.	Unit
Operating current	I_{op}			200	mA
Operating voltage	V_{op}		1.4	2.0	V
Reverse voltage	V_{rev}			2.0	V
Optical output power at 100mA	P_{out}	8	10		mW
Centroid wavelength	λ_C	1165	1170	1175	nm
FWHM of spectrum	$\Delta\lambda$	30	40	50	nm
Operating temperature range	T_{op}	15		60	°C
Chip soldering temperature (20sec)	T_{sol}			330	°C

DIMENSIONS in mm

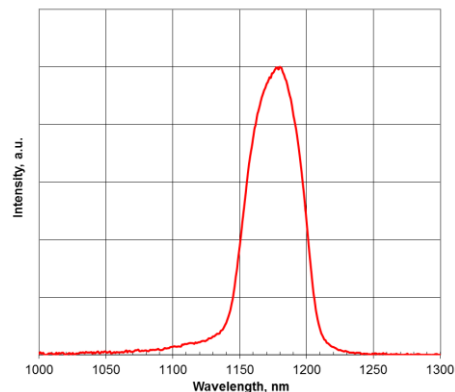
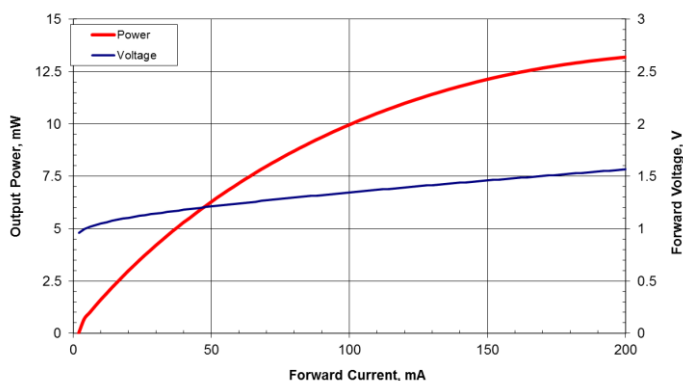


Design:

P-side up;

wire-bondable Au bond pad with current spreaders on top side;

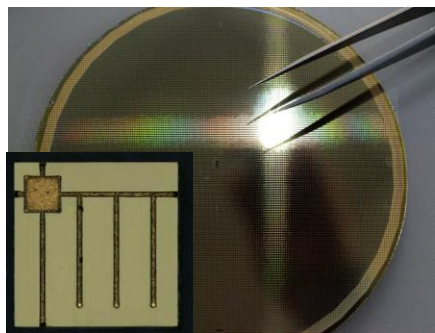
back-side full (100%) area metallization, Au-finished, solderable



NOTE: Innolume product specifications are subject to change without notice

RCLED-1240-3

High Power RCLED Chip – 3mW @ 1240nm



Features:

- Quantum Dot based InAs/AlGaAs/GaAs RCLED chip
- Reduced spectral width and enhanced power due to resonant cavity structure
- Unique wavelength range
- RoHS compliant

Applications:

- Pulse oximetry: Total Hemoglobin, Oxygen Content, Carboxyhemoglobin, Methemoglobin

Specification

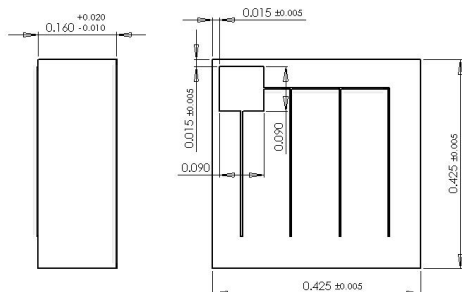
DATE: 14th Feb. 2014

SPECIFICATIONS

Test conditions: CW operation at temperature of 25°C

Parameters	Symb.	Min.	Typ.	Max.	Unit
Operating current	I_{op}			200	mA
Operating voltage	V_{op}		1.3	2.0	V
Reverse voltage	V_{rev}			2.0	V
Optical output power at 100mA	P_{out}	2.5	3.0		mW
Centroid wavelength	λ_C	1235	1240	1245	nm
FWHM of spectrum	$\Delta\lambda$	30	40	50	nm
Operating temperature range	T_{op}	15		60	°C
Chip soldering temperature (20sec)	T_{sol}			330	°C

DIMENSIONS in mm

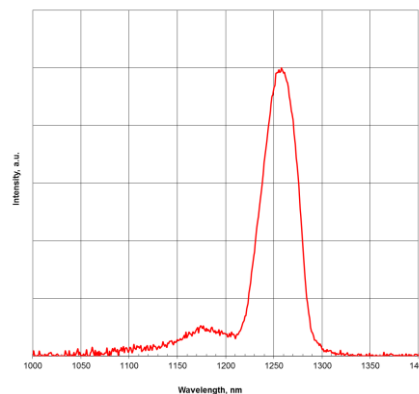
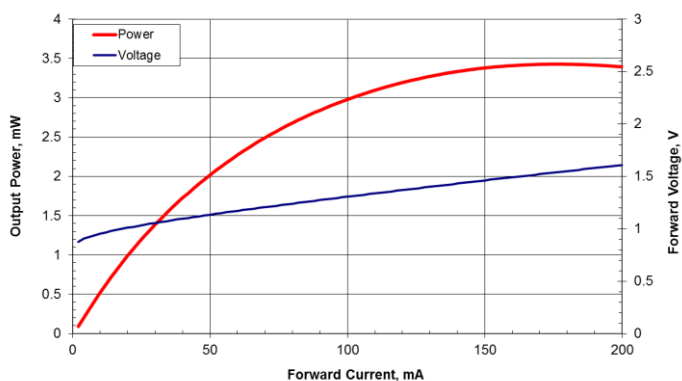


Design:

P-side up;

wire-bondable Au bond pad with current spreaders on top side;

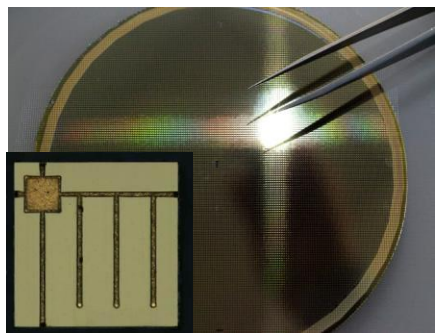
back-side full (100%) area metallization, Au-finished, solderable



NOTE: Innolume product specifications are subject to change without notice

RCLED-1270-3

High Power RCLED Chip – 3mW @ 1270nm



Features:

- Quantum Dot based InAs/AlGaAs/GaAs RCLED chip
- Reduced spectral width and enhanced power due to resonant cavity structure
- Unique wavelength range
- RoHS compliant

Applications:

- Pulse oximetry: Total Hemoglobin, Oxygen Content, Carboxyhemoglobin, Methemoglobin

Specification

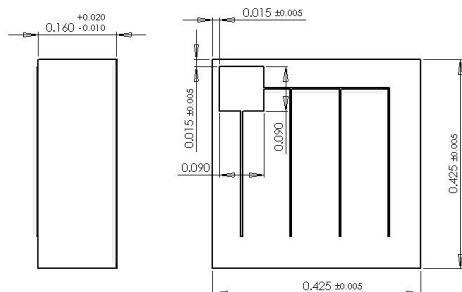
DATE: 14th Feb. 2014

SPECIFICATIONS

Test conditions: CW operation at temperature of 25°C

Parameters	Symb.	Min.	Typ.	Max.	Unit
Operating current	I_{op}			200	mA
Operating voltage	V_{op}		1.3	2.0	V
Reverse voltage	V_{rev}			2.0	V
Optical output power at 100mA	P_{out}	2.5	3.0		mW
Centroid wavelength	λ_C	1235	1240	1245	nm
FWHM of spectrum	$\Delta\lambda$	30	40	50	nm
Operating temperature range	T_{op}	15		60	°C
Chip soldering temperature (20sec)	T_{sol}			330	°C

DIMENSIONS in mm

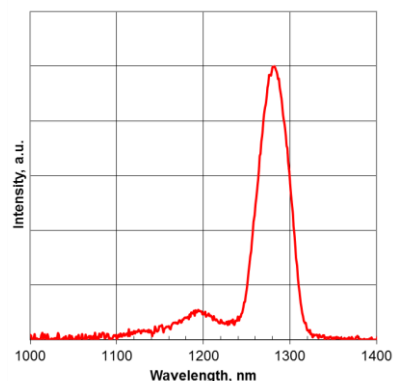
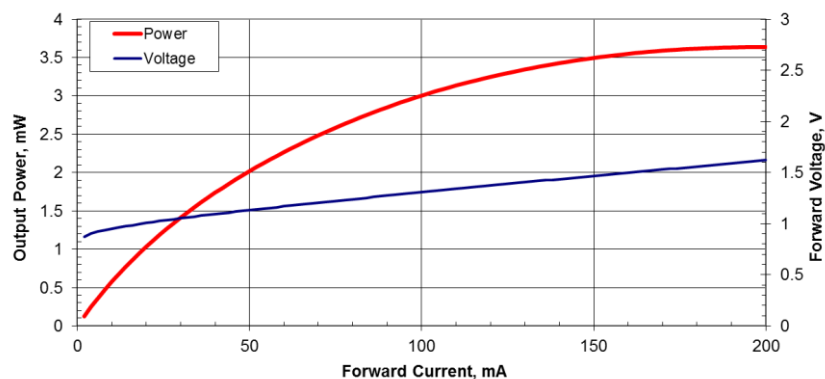


Design:

P-side up;

wire-bondable Au bond pad with current spreaders on top side;

back-side full (100%) area metallization, Au-finished, solderable



NOTE: Innolume product specifications are subject to change without notice